

TSD2150A

Low Vcesat NPN Transistor



SOT-89



Pin Definition:

- 1. Base
- 2. Collector
- 3. Emitter

PRODUCT SUMMARY

BV _{CBO}	80V
BV _{CEO}	50V
Ic	3A
$V_{CE(SAT)}$	0.5V @ I _C / I _B = 2A / 200mA

Ordering Information

Part No.	Package	Packing
TSD2150ACY RM	SOT-89	1Kpcs / 7" Reel

Features

- Low $V_{CE(SAT)}$ 0.1 @ $I_C / I_B = 1A / 50mA$ (Typ.)
- Complementary part with TSB1424A

Structure

- Epitaxial Planar Type
- NPN Silicon Transistor

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V_{CBO}	80	V	
Collector-Emitter Voltage		V _{CEO}	50	V	
Emitter-Base Voltage		V_{EBO}	6	V	
Collector Current	DC		3	Α	
	Pulse	- I _C	6 (note1)		
Collector Power Dissipation		P _D	0.6	W	
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C	

Note: 1. Single pulse, Pw=10ms, Duty≤50%

Electrical Specifications (T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_C = 50uA, I_E = 0$	BV_CBO	80			V
Collector-Emitter Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	BV_CEO	50			V
Emitter-Base Breakdown Voltage	$I_E = 50uA, I_C = 0$	BV_{EBO}	6			V
Collector Cutoff Current	V _{CB} = 60V, I _E = 0	I _{CBO}			0.1	μA
Emitter Cutoff Current	$V_{EB} = 3V, I_{C} = 0$	I _{EBO}			0.1	μA
Collector-Emitter Saturation Voltage	I _C / I _B = 1A / 50mA	V _{CE(SAT)}		0.1	0.25	V
	I _C / I _B = 2A / 200mA	V _{CE(SAT)}		0.25	0.5	
Base-Emitter Saturation Voltage	I _C / I _B = 2A / 200mA	$V_{BE(SAT)}$			2	V
DC Current Transfer Ratio	V _{CE} = 2V, I _C = 100mA	h _{FE} 1	180			
	V _{CE} = 2V, I _C = 500mA	h _{FE} 2	200		400	
	V _{CE} = 2V, I _C = 1A	h _{FE} 3	150			
Transition Frequency	V _{CE} =5V, I _E =0.1A, f=100MHz	f _T	-	90	1	MHz
Output Capacitance	V _{CB} = 10V, f=1MHz	Cob		45		pF

Note: Pulse test: pulse width ≤380µs, Duty cycle≤2%

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^{2.} When mounted on a 40 x 50 x 0.7mm ceramic board.





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Electrical Characteristics Curves (T_A=25°C, unless otherwise noted)

Figure 1. DC Current Gain

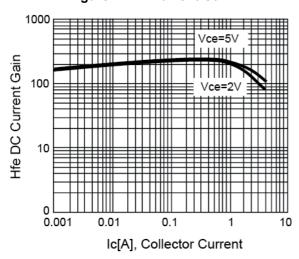


Figure 3. $V_{\text{BE(SAT)}}$ v.s. Collector Current

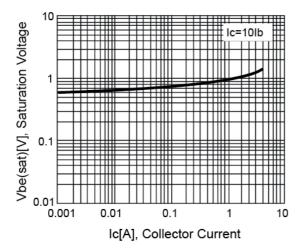


Figure 2. V_{CE(SAT)} v.s. Collector Current

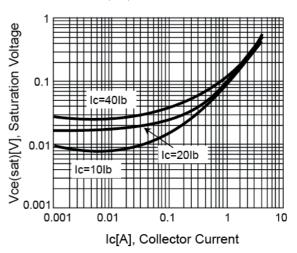
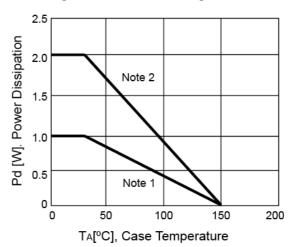


Figure 4. Power Derating Curve



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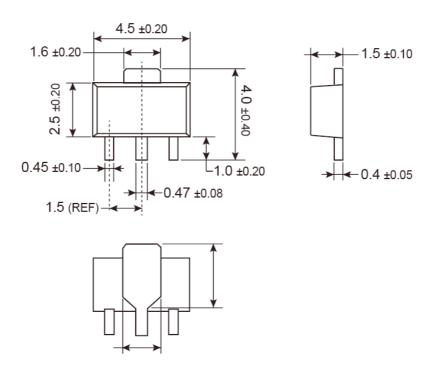
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TSD2150A

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SOT-89 Mechanical Drawing



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Unit: Millimeters

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